

MOS FIELD EFFECT TRANSISTOR

NP40N055ELE, NP40N055KLE NP40N055CLE, NP40N055DLE, NP40N055MLE, NP40N055NLE

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

<R> ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP40N055ELE-E1-AY ^{Note1, 2}	Pure Sn (Tin)	Tape 800 p/reel	TO-263 (MP-25ZJ) typ. 1.4 g
NP40N055ELE-E2-AY ^{Note1, 2}			
NP40N055KLE-E1-AY ^{Note1}			TO-263 (MP-25ZK) typ. 1.5 g
NP40N055KLE-E2-AY ^{Note1}			
NP40N055CLE-S12-AZ ^{Note1, 2}	Sn-Ag-Cu	Tube 50 p/tube	TO-220 (MP-25) typ. 1.9 g
NP40N055DLE-S12-AY ^{Note1, 2}	Pure Sn (Tin)		TO-262 (MP-25 Fin Cut) typ. 1.8 g
NP40N055MLE-S18-AY ^{Note1}			TO-220 (MP-25K) typ. 1.9 g
NP40N055NLE-S18-AY ^{Note1}			TO-262 (MP-25SK) typ. 1.8 g

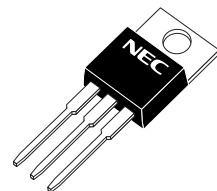
Notes 1. Pb-free (This product does not contain Pb in the external electrode.)

2. Not for new design

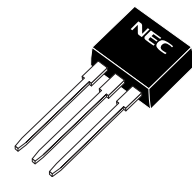
FEATURES

- Channel temperature 175 degree rated
- Super low on-state resistance
 $R_{DS(on)1} = 23 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 20 \text{ A)}$
 $R_{DS(on)2} = 28 \text{ m}\Omega \text{ MAX. (} V_{GS} = 5.0 \text{ V, } I_D = 20 \text{ A)}$
 $R_{DS(on)3} = 32 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 20 \text{ A)}$
- Low input capacitance
 $C_{iss} = 1300 \text{ pF TYP.}$
- Built-in gate protection diode

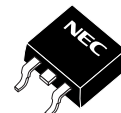
(TO-220)



(TO-262)



(TO-263)



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 Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	55	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) (T _C = 25°C)	I _{D(DC)}	±40	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±100	A
Total Power Dissipation (T _A = 25°C)	P _T	1.8	W
Total Power Dissipation (T _C = 25°C)	P _T	66	W
Channel Temperature	T _{ch}	175	°C
Storage Temperature	T _{stg}	-55 to +175	°C
Single Avalanche Current ^{Note2}	I _{AS}	29/21/8	A
Single Avalanche Energy ^{Note2}	E _{AS}	0.8/44/64	mJ

Notes 1. PW ≤ 10 μs, Duty cycle ≤ 1%

2. Starting T_{ch} = 25°C, V_{DD} = 28 V, R_G = 25 Ω, V_{GS} = 20 → 0 V (see **Figure 4.**)

THERMAL RESISTANCE

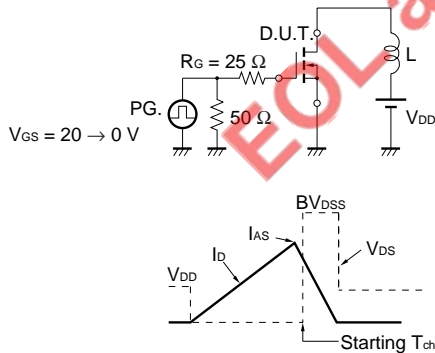
Channel to Case Thermal Resistance	R _{th(ch-C)}	2.27	°C/W
Channel to Ambient Thermal Resistance	R _{th(ch-A)}	83.3	°C/W

EOL announced Product

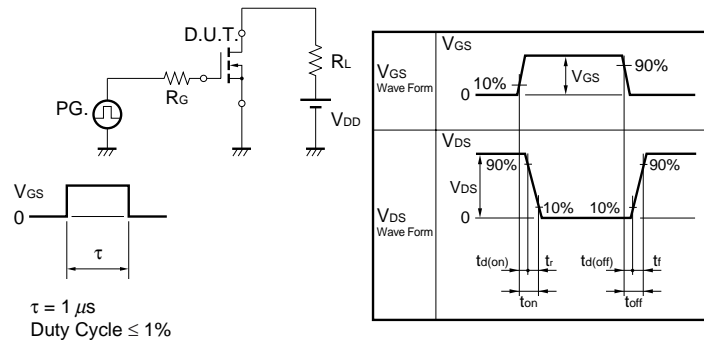
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 55\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 10	μA
Gate to Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.5	2.0	2.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$	8	18		S
Drain to Source On-state Resistance	$R_{DS(on)1}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		18	23	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS} = 5.0\text{ V}, I_D = 20\text{ A}$		21	28	$\text{m}\Omega$
	$R_{DS(on)3}$	$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		24	32	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = 25\text{ V},$ $V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		1300	1950	pF
Output Capacitance	C_{oss}			190	280	pF
Reverse Transfer Capacitance	C_{rss}			92	170	pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 28\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V},$ $R_G = 1\ \Omega$		14	32	ns
Rise Time	t_r			8.4	21	ns
Turn-off Delay Time	$t_{d(off)}$			39	78	ns
Fall Time	t_f			7.4	19	ns
Total Gate Charge	Q_{G1}	$V_{DD} = 44\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		27	41	nC
	Q_{G2}	$V_{DD} = 44\text{ V},$ $V_{GS} = 5.0\text{ V},$ $I_D = 40\text{ A}$		15	23	nC
Gate to Source Charge	Q_{GS}			5		nC
Gate to Drain Charge	Q_{GD}			8		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	$I_F = 40\text{ A}, V_{GS} = 0\text{ V}$		1.0		V
Reverse Recovery Time	t_{rr}	$I_F = 40\text{ A}, V_{GS} = 0\text{ V},$ $di/dt = 100\text{ A}/\mu\text{s}$		40		ns
Reverse Recovery Charge	Q_{rr}			50		nC

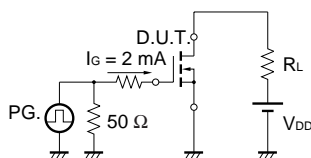
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



TYPICAL CHARACTERISTICS (T_A = 25°C)

Figure1. DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

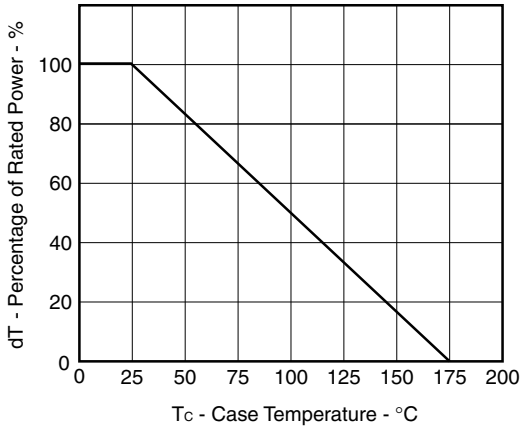


Figure2. TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

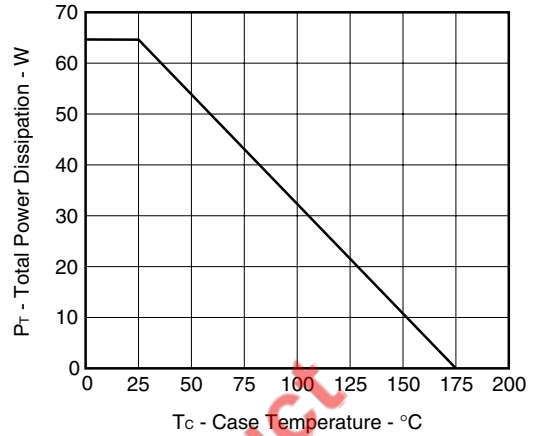


Figure3 FORWARD BIAS SAFE OPERATING AREA

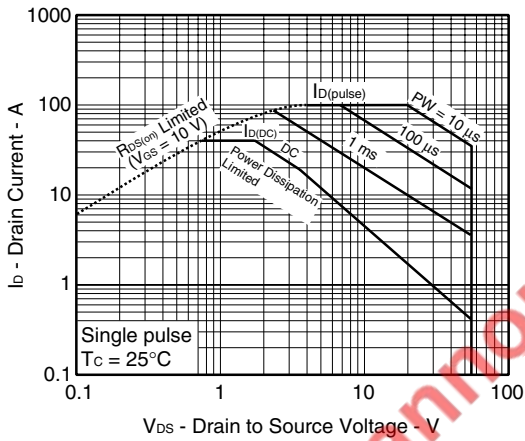


Figure4. SINGLE AVALANCHE ENERGY DERATING FACTOR

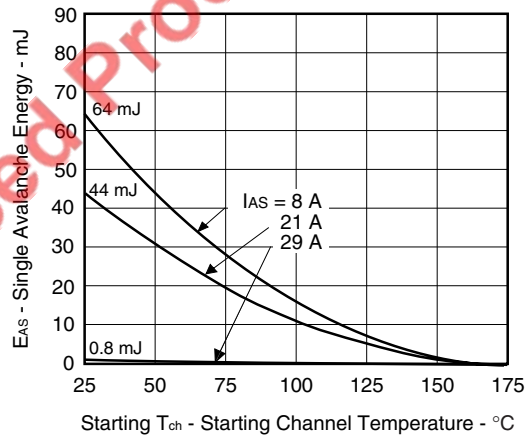


Figure5. TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

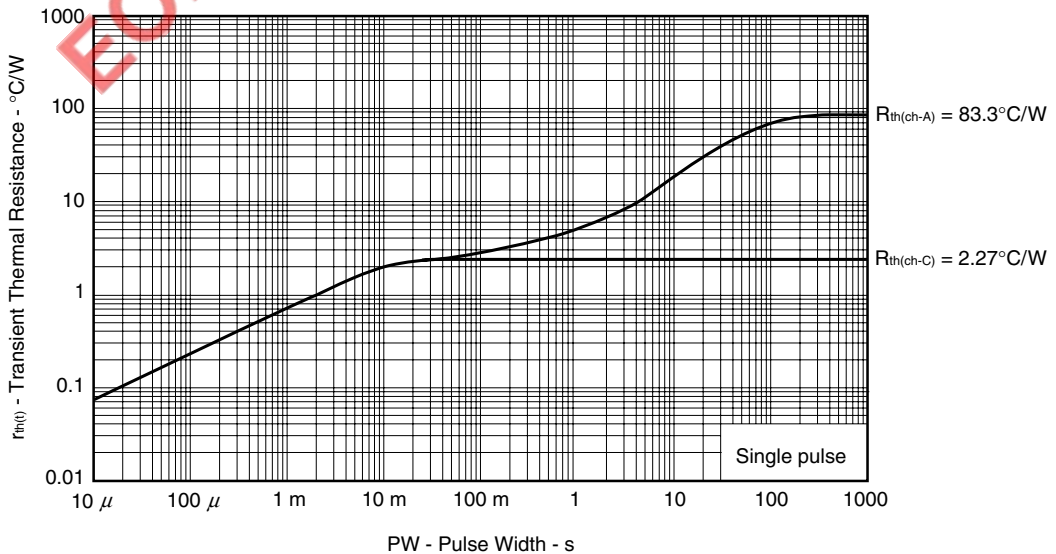


Figure6. FORWARD TRANSFER CHARACTERISTICS

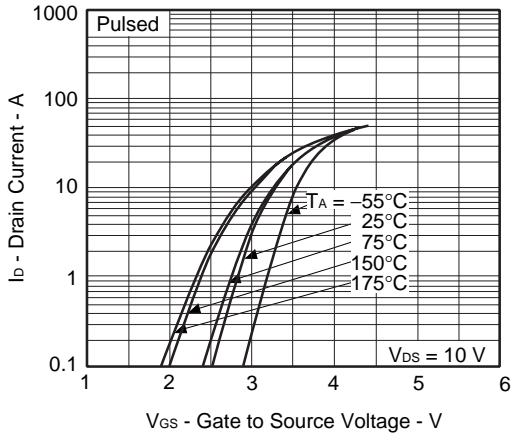


Figure7. DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

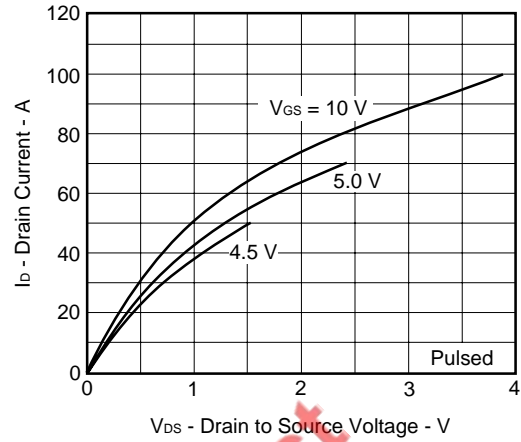


Figure8. FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

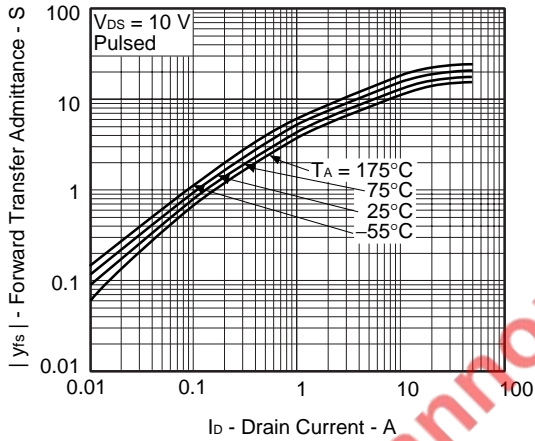


Figure9. DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

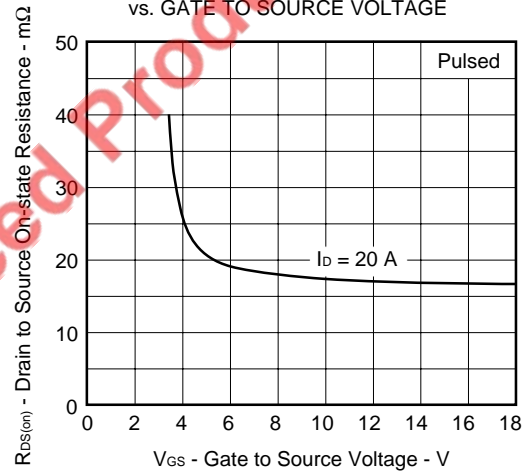


Figure10. DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

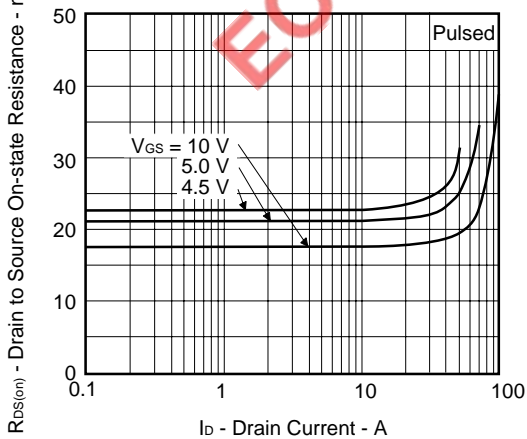


Figure11. GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

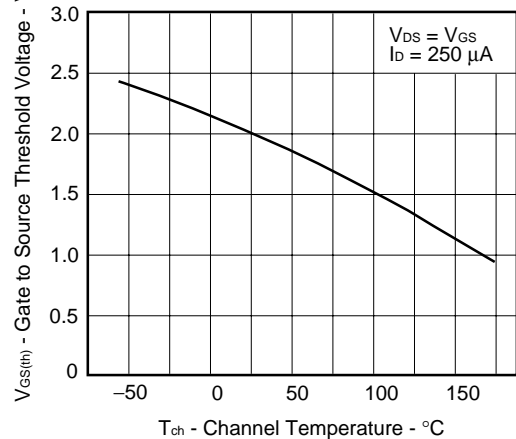


Figure12. DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

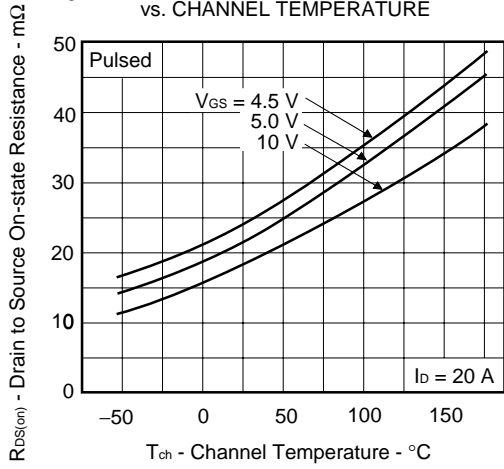


Figure13. SOURCE TO DRAIN DIODE FORWARD VOLTAGE

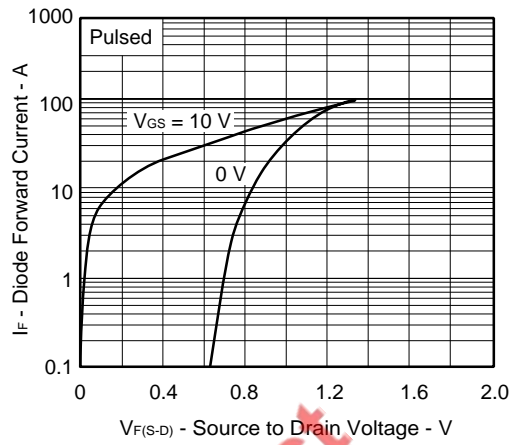


Figure14. CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

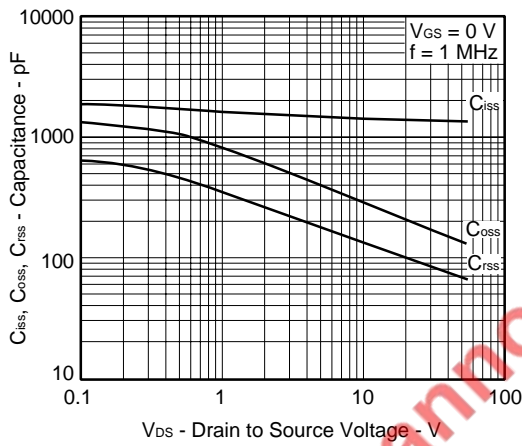


Figure15. SWITCHING CHARACTERISTICS

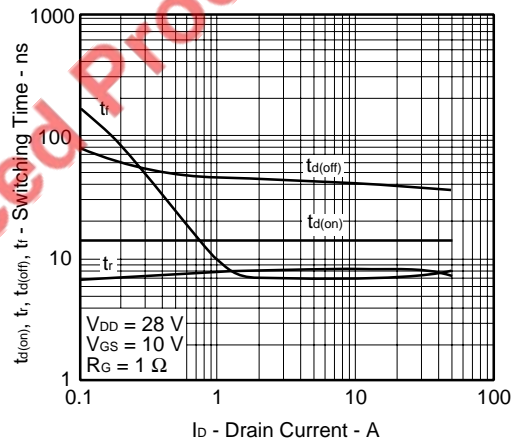


Figure16. REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

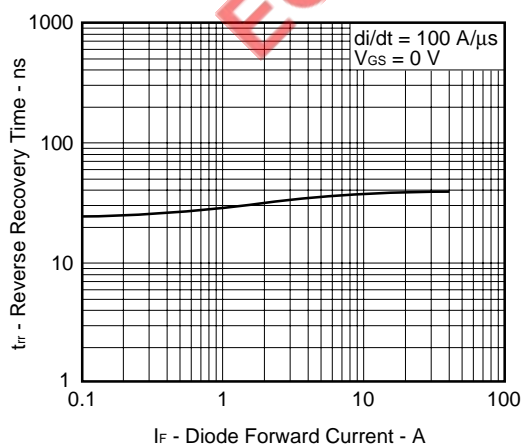
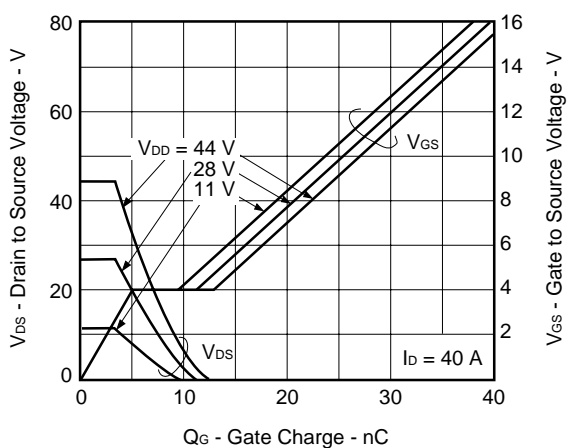
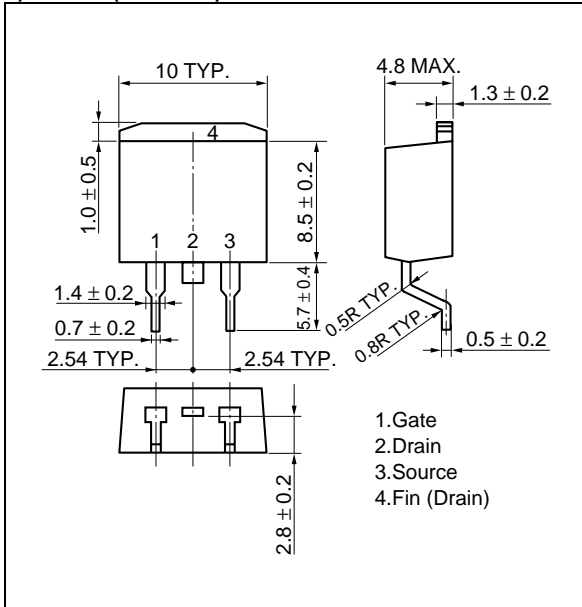


Figure17. DYNAMIC INPUT/OUTPUT CHARACTERISTICS

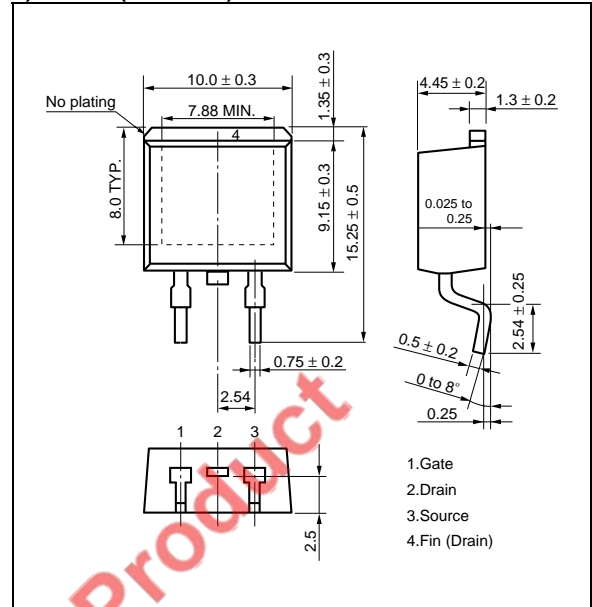


<R> PACKAGE DRAWINGS (Unit: mm)

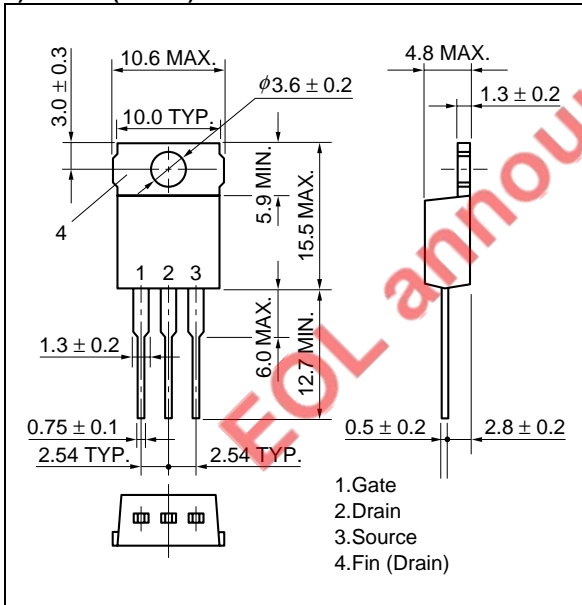
1) TO-263 (MP-25ZJ) ^{Note}



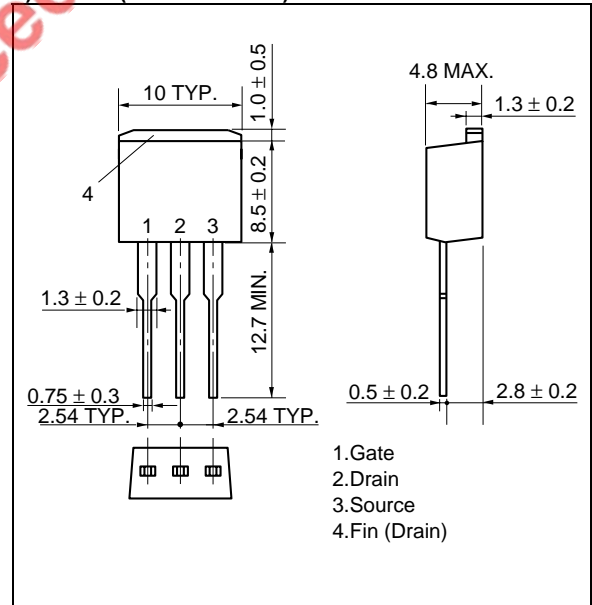
2) TO-263 (MP-25ZK)



3) TO-220 (MP-25) ^{Note}

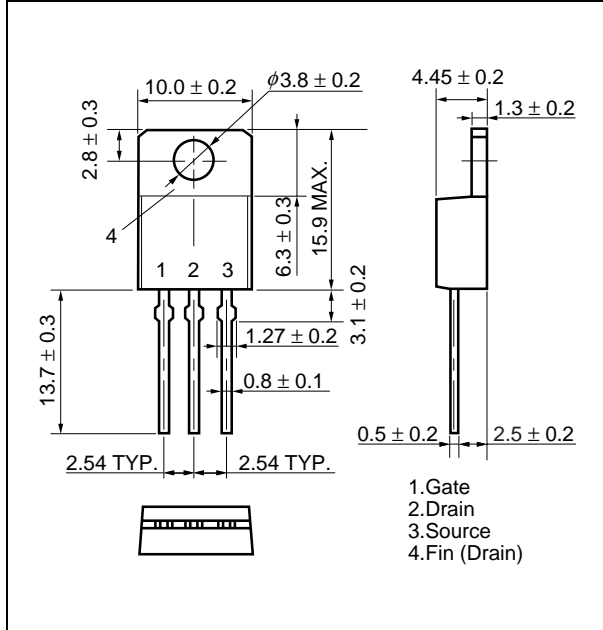


4) TO-262 (MP-25 Fin Cut) ^{Note}

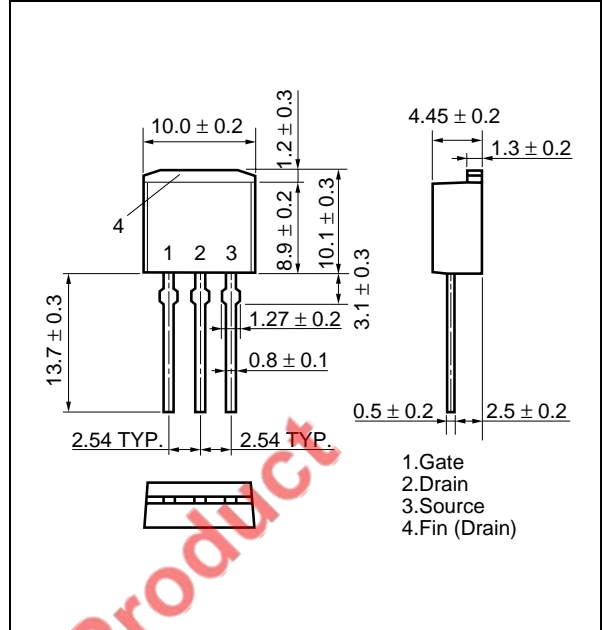


Note Not for new design

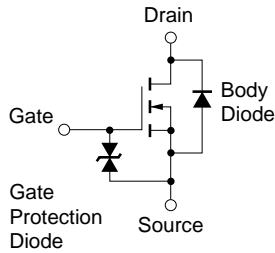
5) TO-220 (MP-25K)



6) TO-262 (MP-25SK)



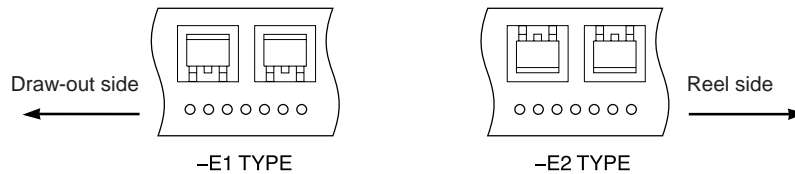
EQUIVALENT CIRCUIT



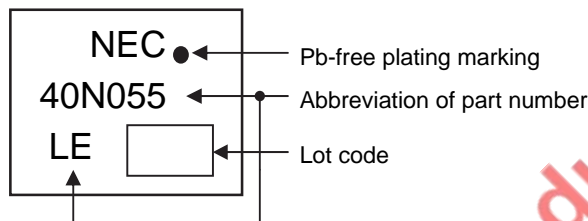
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

<R> **TAPE INFORMATION**

There are two types (-E1, -E2) of taping depending on the direction of the device.



<R> **MARKING INFORMATION**



<R> **RECOMMENDED SOLDERING CONDITIONS**

These products should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (<http://www.necel.com/pkg/en/mount/index.html>)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow MP-25ZJ, MP-25ZK	Maximum temperature (Package's surface temperature): 260°C or below Time at maximum temperature: 10 seconds or less Time of temperature higher than 220°C: 60 seconds or less Preheating time at 160 to 180°C: 60 to 120 seconds Maximum number of reflow processes: 3 times Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	IR60-00-3
Wave soldering MP-25, MP-25K, MP-25SK, MP-25 Fin Cut	Maximum temperature (Solder temperature): 260°C or below Time: 10 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	THDWS
Partial heating MP-25ZJ, MP-25ZK, MP-25K, MP-25SK	Maximum temperature (Pin temperature): 350°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P350
Partial heating MP-25, MP-25 Fin Cut	Maximum temperature (Pin temperature): 300°C or below Time (per side of the device): 3 seconds or less Maximum chlorine content of rosin flux: 0.2% (wt.) or less	P300

Caution Do not use different soldering methods together (except for partial heating).